

PHOTOTRANSISTOR

Part Number: AM4457P3C

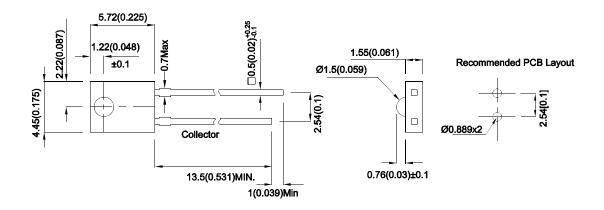
Features

- Mechanically and spectrally matched to infrared emitting LED lamp.
- RoHS compliant.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



- All dimensions are in millimeters (inches).
 Tolerance is ±0.25(0.01") unless otherwise noted.
- 3. Lead spacing is measured where the leads emerge from the package.

 4. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

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Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
VBR CEO	Collector-to-Emitter Breakdown Voltage	30			V	Ic=100uA Ee=0mW/c m²
VBR ECO	Emitter-to-Collector Breakdown Voltage	5			V	IE=100uA Ee=0mW/c m²
VCE (SAT)	Collector-to-Emitter Saturation Voltage			0.8	V	Ic=2mA Ee=20mW/c m³
I CEO	Collector Dark Current			100	nA	VcE=10V Ee=0mW/c m³
TR	Rise Time (10% to 90%)		15		us	VcE = 5V Ic=1mA RL=1000Ω
TF	Fall Time (90% to 10%)		15		us	
I (ON)	On State Collector Current	0.35	0.8		mA	VcE = 5V Ee=1mW/c m ² λ=940nm

Absolute Maximum Ratings at TA=25°C

Parameter	Max.Ratings			
Collector-to-Emitter Voltage	30V			
Emitter-to-Collector Voltage	5V			
Power Dissipation at (or below) 25°C Free Air Temperature	100mW			
Operating Temperature	-40°C To +85°C			
Storage Temperature	-40°C To +85°C			
Lead Soldering Temperature (>5mm for 5sec)	260°C			

Note:

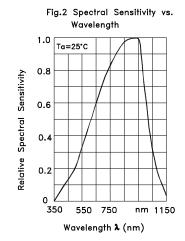
Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs.

Ambient Temperature

Ambient Temperature $T_A(^{\circ}C)$

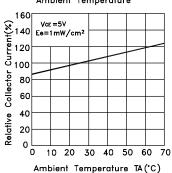


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Fig.3 Relative Collector Current vs. Ambient Temperature



70

Fig.5 Collector Dark Current vs.

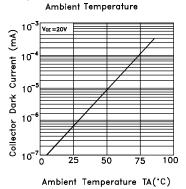


Fig.6 Collector Current vs.

mW/cm²10¹

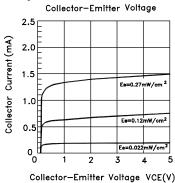
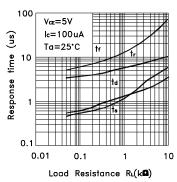
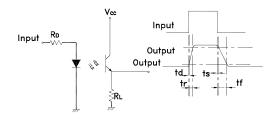


Fig.7 Response Time vs. Load Resistance

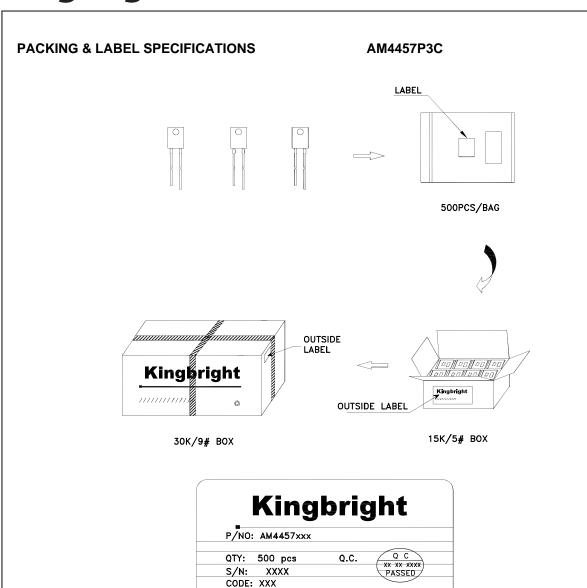


Test Circuit for Response Time



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LOT NO:

1. The information included in this document reflects representative usage scenarios and is intended for technical reference only.

RoHS Compliant

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